International Rectifier

AUTOMOTIVE GRADE

AUIRF6218S AUIRF6218L

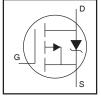
HEXFET® Power MOSFET

Features

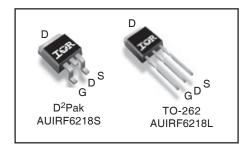
- Advanced Planar Technology
- Low On-Resistance
- P-Channel
- Dynamic dV/dT Rating
- 175°C Operating Temperature
- · Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Timax
- Lead-Free, RoHS Compliant
- Automotive Qualified *

Description

Specifically designed for Automotive applications, this cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and rugge-dized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.



V _{(BR)DSS}	-150V
R _{DS(on)} max	150m Ω
I _D	-27A



G	D	S
Gate	Drain	Source

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
V _{DS}	Drain-to-Source Voltage	-150	V
V _{GS}	Gate-to-Source Voltage	± 20	
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	-27	Α
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	-19	
I _{DM}	Pulsed Drain Current ①	-110	
P _D @ T _C = 25°C	Maximum Power Dissipation	250	W
	Linear Derating Factor	1.6	W/°C
E _{AS}	Single Pulse Avalanche Energy (Thermally Limited)②	210	mJ
I _{AR}	Avalanche Current ①	-16	А
dv/dt	Peak Diode Recovery dv/dt ③	8.2	V/ns
TJ	Operating Junction and	-55 to + 175	°C
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from cas	300	
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Тур.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ^⑤		0.61	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mounted, steady state) (6)		40	

Static Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	-150			V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient		-0.17		V/°C	Reference to 25°C, $I_D = -1mA$
R _{DS(on)}	Static Drain-to-Source On-Resistance		120	150	mΩ	V _{GS} = -10V, I _D = -16A ⊕
V _{GS(th)}	Gate Threshold Voltage	-3.0		-5.0	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
gfs	Forward Transconductance	11			S	$V_{DS} = -50V, I_{D} = -16A$
I _{DSS}	Drain-to-Source Leakage Current			-25	μΑ	$V_{DS} = -120V, V_{GS} = 0V$
				-250		$V_{DS} = -120V$, $V_{GS} = 0V$, $T_{J} = 150$ °C
I _{GSS}	Gate-to-Source Forward Leakage			-100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage			100		$V_{GS} = 20V$

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Conditions
Qg	Total Gate Charge		71	110		I _D = -16A
Q _{gs}	Gate-to-Source Charge		21		nC	V _{DS} = -120V
Q_{gd}	Gate-to-Drain ("Miller") Charge		32			V _{GS} = -10V ⊕
t _{d(on)}	Turn-On Delay Time		21			$V_{DD} = -75V$
t _r	Rise Time		70		ns	I _D = -16A
t _{d(off)}	Turn-Off Delay Time		35]	$R_G = 3.9\Omega$
t _f	Fall Time		30		1	V _{GS} = -10V ⊕
C _{iss}	Input Capacitance		2210			$V_{GS} = 0V$
Coss	Output Capacitance		370		1	V _{DS} = -25V
C _{rss}	Reverse Transfer Capacitance		89		pF	f = 1.0 MHz
Coss	Output Capacitance		2220			$V_{GS} = 0V$, $V_{DS} = -1.0V$, $f = 1.0MHz$
Coss	Output Capacitance		170		1	$V_{GS} = 0V$, $V_{DS} = -120V$, $f = 1.0MHz$
Coss eff.	Effective Output Capacitance		340		1	$V_{GS} = 0V$, $V_{DS} = 0V$ to -120V

Diode Characteristics

	Parameter	Min.	Тур.	Max.	Units	Conditions
Is	Continuous Source Current			-27		MOSFET symbol
	(Body Diode)				Α	showing the
I _{SM}	Pulsed Source Current			-110		integral reverse
	(Body Diode) ①					p-n junction diode.
V_{SD}	Diode Forward Voltage			-1.6	V	$T_J = 25^{\circ}C$, $I_S = -16A$, $V_{GS} = 0V \oplus$
t _{rr}	Reverse Recovery Time		150		ns	$T_J = 25^{\circ}C$, $I_F = -16A$, $V_{DD} = -25V$
Q _{rr}	Reverse Recovery Charge		860		nC	di/dt = -100A/µs

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^{\circ}C$, L = 1.6mH, $R_G = 25\Omega$, $I_{AS} = -17A$.
- $\label{eq:loss_def} \mbox{ } \mbox{I}_{SD} \leq \mbox{-17A, di/dt} \leq \mbox{-520A/}\mu\mbox{s, V}_{DD} \leq \mbox{V}_{(BR)DSS}, \mbox{T}_{J} \leq \mbox{175}^{\circ}\mbox{C}.$
- 4 Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$.
- $\ ^{\textcircled{5}}$ R $_{\theta}$ is measured at T $_{J}$ of approximately 90°C.
- ® When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.

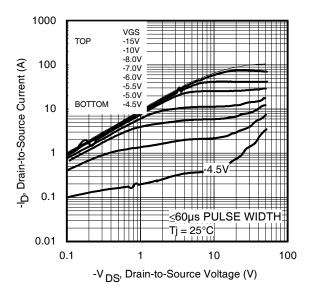
Qualification Information[†]

		Automotive					
		(per AEC-Q101)					
Qualification Level Comments: This part number(s) passed Automotive qualification Industrial and Consumer qualification level is granted by extension of the Automotive level.							
Maiatura	Sanaitivity Laval	TO-262	N/A				
worsture s	Sensitivity Level	D ² Pak MSL1					
	Machine Model	Class M4 (+/- 600V) ^{††}					
			AEC-Q101-002				
F0.D	Human Body Model		Class H2 (+/- 3000V) ^{††}				
ESD		AEC-Q101-001					
Charged Device Mod		Class C5 (+/- 2000V) ^{††}					
		AEC-Q101-005					
RoHS Con	npliant		Yes				

[†] Qualification standards can be found at International Rectifier's web site: http://www.irf.com/

3

^{††} Highest passing voltage.



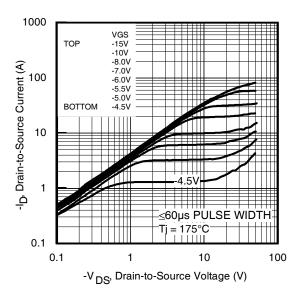
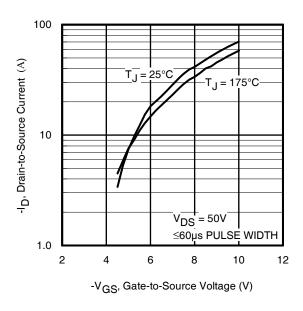


Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics



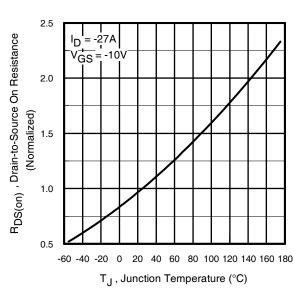
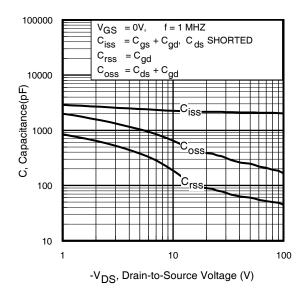


Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance vs. Temperature



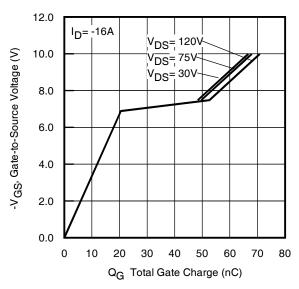
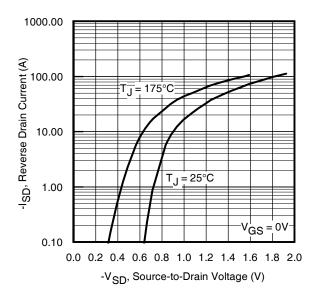


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage



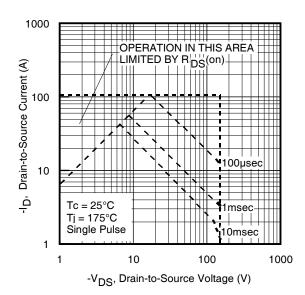


Fig 7. Typical Source-Drain Diode Forward Voltage

Fig 8. Maximum Safe Operating Area

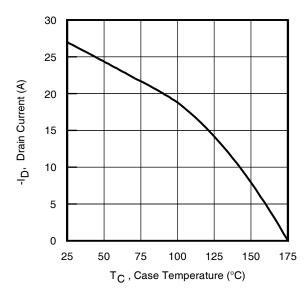


Fig 9. Maximum Drain Current vs. Ambient Temperature

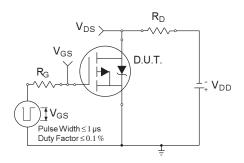


Fig 10a. Switching Time Test Circuit

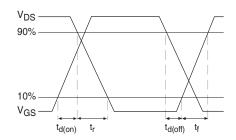


Fig 10b. Switching Time Waveforms

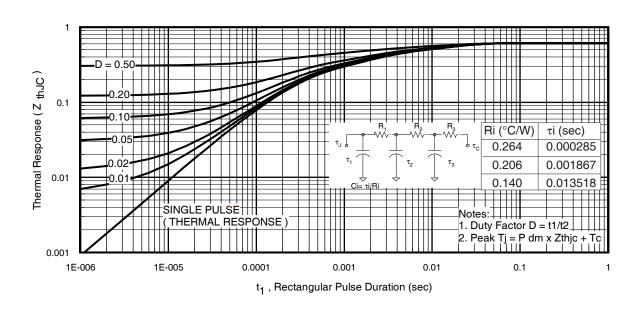
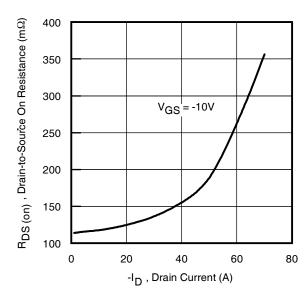


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



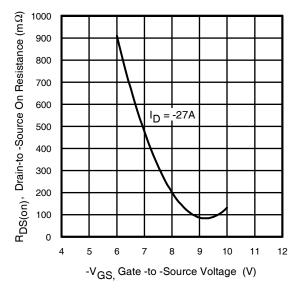


Fig 12. On-Resistance vs. Drain Current

Fig 13. On-Resistance vs. Gate Voltage

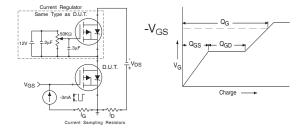


Fig 14a&b. Basic Gate Charge Test Circuit and Waveform

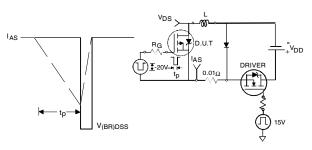


Fig 15a&b. Unclamped Inductive Test circuit and Waveforms

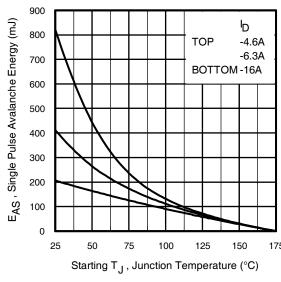
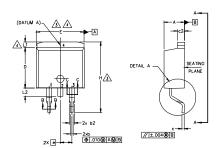


Fig 15c. Maximum Avalanche Energy vs. Drain Current

D²Pak Package Outline

(Dimensions are shown in millimeters (inches))





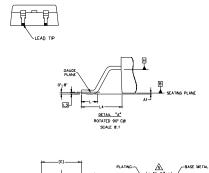
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- 2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].

3.\Dimension D & E DO NOT INCLUDE MOLD FLASH, MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.

4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.

5. DIMENSION 61 AND c1 APPLY TO BASE METAL ONLY.

- 6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
- 7. CONTROLLING DIMENSION: INCH.
- 8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.



5 Y		DIMEN	ISIONS		N
M B	MILLIM	ETERS	INC	HES	Ĭ
0	MIN.	MAX.	MIN.	MAX.	Š

Ř	MILLIM	FIERS	ERS INCHES		
Г 0 В	MIN.	MAX.	MIN.	MAX.	E S
Α	4.06	4,83	.160	.190	
Α1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	5
b2	1,14	1.78	.045	.070	
b3	1,14	1.73	.045	.068	5
С	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1,14	1,65	.045	.065	
D	8.38	9.65	.330	.380	3
D1	6.86	-	.270		4
Ε	9.65	10,67	.380	.420	3,4
E1	6.22	-	.245		4
e	2.54	BSC	.100	BSC	
Н	14,61	15.88	.575	.625	
L	1,78	2.79	.070	.110	
L1	-	1.65	-	.066	4
L2	1,27	1.78	-	.070	

.010 BSC

.188

LEAD ASSIGNMENTS

HEXFET

1.- GATE 2. 4.- DRAIN 3.- SOURCE

IGBTs, CoPACK

1.- GATE

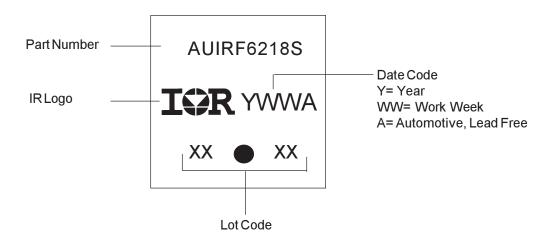
DIODES

1.- ANODE * 4.- CATHODE 3.- ANODE

* PART DEPENDENT.

D²Pak Part Marking Information

4



L3

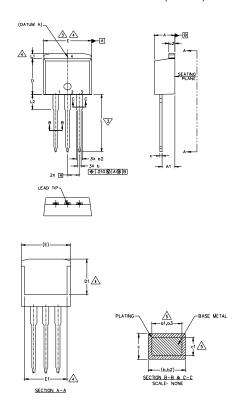
0.25 BSC

4,78

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

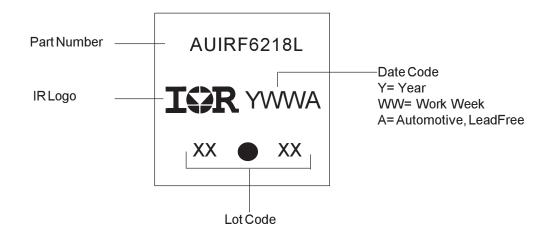
TO-262 Package Outline

Dimensions are shown in millimeters (inches)



S Y M			Z		
МВОЬ	MILLIM	ETERS	INCHES		NOLEN
L	MIN.	MAX.	MIN.	MAX.	S
Α	4.06	4.83	.160	.190	
A1	2.03	3.02	.080	.119	
ь	0.51	0.99	.020	.039	
ь1	0.51	0.89	.020	.035	5
ь2	1.14	1.78	.045	.070	
ьз	1.14	1.73	.045	.068	5
С	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1.14	1.65	.045	.065	
D	8.38	9.65	.330	.380	3
D1	6.86	-	.270	_	4
Ε	9.65	10.67	.380	.420	3,4
E1	6.22	-	.245		4
e	2.54	BSC	.100	BSC	
L	13.46	14.10	.530	.555	
L 1	_	1.65	_	.065	4
L2	3.56	3.71	.140	,146	

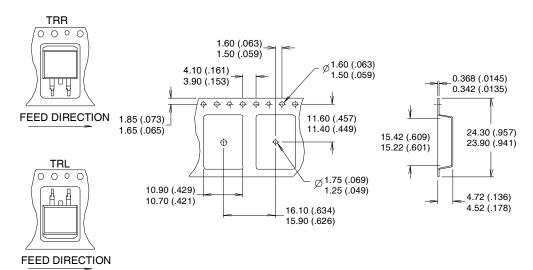
TO-262 Part Marking Information

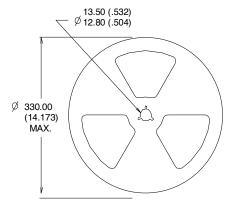


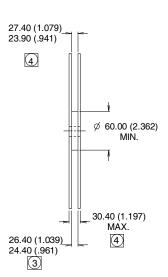
Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)







NOTES:

- 1. COMFORMS TO EIA-418.
- CONTROLLING DIMENSION: MILLIMETER.
- 2. CONTROLLING DIMENSION: MILI DIMENSION MEASURED @ HUB.
- 4 INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Ordering Information

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRF6218L	TO-262	Tube	50	AUIRF6218L
AUIRF6218S	D2Pak	Tube	50	AUIRF6218S
		Tape and Reel Left	800	AUIRF6218STRL
		Tape and Reel Right	800	AUIRF6218STRR

AUIRF6218S/L

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